



MMBT4401T

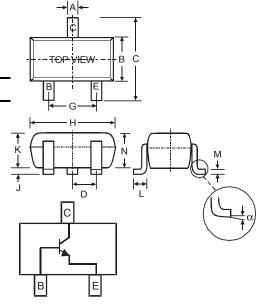
NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMBT4403T)
- Lead Free/RoHS Compliant (Note 2)
- "Green" Device (Note 3 and 4)

Mechanical Data

- Case: SOT-523
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: 2X, See Page 4
- Ordering & Date Code Information: See Page 4
- Weight: 0.002 grams (approximate)



SOT-523									
Dim	Min	Max	Тур						
Α	0.15	0.30	0.22						
В	0.75	0.85	0.80						
С	1.45	1.75	1.60						
D		_	0.50						
G	0.90	1.10	1.00						
Н	1.50	1.70	1.60						
J	0.00	0.10	0.05						
K	0.60	0.80	0.75						
L	0.10	0.30	0.22						
М	0.10	0.20	0.12						
N	0.45	0.65	0.50						
α	0°	8°	_						
All Dimensions in mm									

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Collector-Base Voltage		V_{CBO}	60	V
Collector-Emitter Voltage		V _{CEO}	40	V
Emitter-Base Voltage		V_{EBO}	6.0	V
Collector Current – Continuous	(Note 1)	Ic	600	mA
Power Dissipation	(Note 1)	P_d	150	mW
Thermal Resistance, Junction to Ambient	(Note 1)	$R_{ hetaJA}$	833	°C/W
Operating and Storage Temperature Range		T _j , T _{STG}	-55 to +150	°C

Notes:

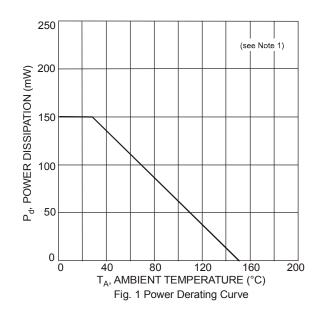
- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 2. No purposefully added lead
- 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 4. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

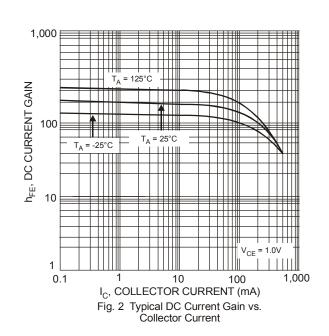


Electrical Characteristics @TA = 25°C unless otherwise specified

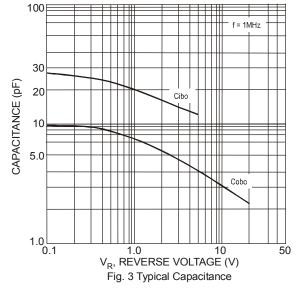
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	60		V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40		V	$I_C = 1.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0		V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	I _{CEX}	_	100	nA	V _{CE} = 35V, V _{EB(OFF)} = 0.4V
Base Cutoff Current	I _{BL}	_	100	nA	V _{CE} = 35V, V _{EB(OFF)} = 0.4V
ON CHARACTERISTICS (Note 5)					
DC Current Gain	h _{FE}	20 40 80 100 40	 300 	-	$\begin{split} I_{C} &= 100 \mu \text{A}, \ V_{CE} = 1.0 \text{V} \\ I_{C} &= 1.0 \text{mA}, \ V_{CE} = 1.0 \text{V} \\ I_{C} &= 10 \text{mA}, \ V_{CE} = 1.0 \text{V} \\ I_{C} &= 150 \text{mA}, \ V_{CE} = 1.0 \text{V} \\ I_{C} &= 500 \text{mA}, \ V_{CE} = 2.0 \text{V} \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.40 0.75	>	$I_C = 150 \text{mA}, I_B = 15 \text{mA}$ $I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Base-Emitter Saturation Voltage		0.75 —	0.95 1.2	٧	$I_C = 150$ mA, $I_B = 15$ mA $I_C = 500$ mA, $I_B = 50$ mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	_	6.5	pF	$V_{CB} = 5.0V$, $f = 1.0MHz$, $I_E = 0$
Input Capacitance	C _{ibo}	_	30	pF	$V_{EB} = 0.5V$, $f = 1.0MHz$, $I_C = 0$
Input Impedance	h _{ie}	1.0	15	kΩ	
Voltage Feedback Ratio	h _{re}	0.1	8.0	x 10 ⁻⁴	V _{CE} = 10V, I _C = 1.0mA,
Small Signal Current Gain	h _{fe}	40	500		f = 1.0kHz
Output Admittance	h _{oe}	1.0	30	μS	
Current Gain-Bandwidth Product	f _T	250		MHz	$V_{CE} = 10V, I_{C} = 20mA,$ f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	_	15	ns	V _{CC} = 30V, I _C = 150mA,
Rise Time	t _r	_	20	ns	$V_{BE(off)} = 2.0V, I_{B1} = 15mA$
Storage Time	ts	_	225	ns	V _{CC} = 30V, I _C = 150mA,
Fall Time	t _f	_	30	ns	$I_{B1} = I_{B2} = 15mA$

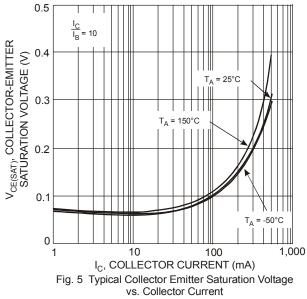
Notes: 5. Short duration pulse test used to minimize self-heating effect.











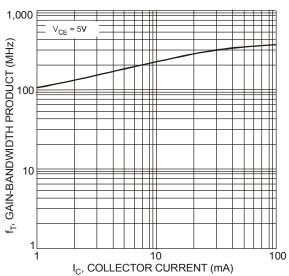
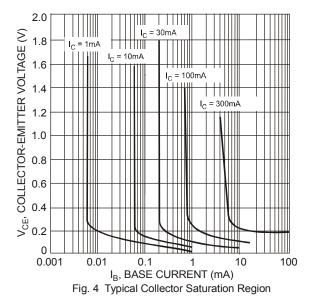


Fig. 7 Typical Gain-Bandwidth Product vs. Collector Current



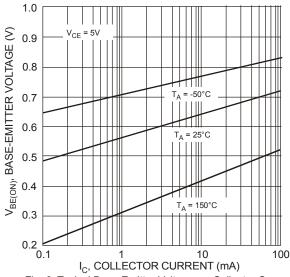


Fig. 6 Typical Base-Emitter Voltage vs. Collector Current

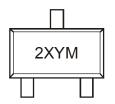


Ordering Information (Note 6)

Device		Packaging	Shipping		
MMBT4401T-7-	F	SOT-523	3000/Tape & Reel		

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



2X = Product Type Marking Code YM = Date Code Marking Y = Year (ex: T = 2006) M = Month (ex: 9 = September)

Date Code Key

Year	2002	2003	2004	2005	200)6 20	007	2008	2009	2010	2011	2012
Code	N	Р	R	S	Т		IJ	V	W	Х	Υ	Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	j Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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